

ABSTRACT

To provide a wafer support and a semiconductor substrate processing method by which dopants released from a rear surface of a semiconductor substrate can be adequately restrained from reaching a top surface of a semiconductor substrate and a reaction gas can be restrained from reaching a rear surface of the semiconductor substrate. A silicon semiconductor wafer 7 is set on a wafer supporting portion 2 of a wafer support 1, a space is formed between the silicon semiconductor wafer 7 and the counterbored portion 2a, a hydrogen gas 5 flows through a gas supplying path 6, provided in a wafer support rotating member 6a positioned at a central region of the wafer support 1, and flows, via gas supplying penetrating hole portions 3 formed in the central region of the counterbored portion 2a, along a surface of the silicon semiconductor wafer 7 in the space between the semiconductor wafer 7 and the counterbored portion 2a, and hydrogen gas 5 is then discharged from the wafer support 1 upon flowing through the gas discharging penetrating hole portions 4 that are inclined with respect to a vertical direction and put the counterbored portion 2a in communication with an outer surface of the wafer support 1 at the side opposite the side on which the semiconductor wafer 7 is set.